

9097250 TOSHIBA (DISCRETE/OPTO)

67C 09294 D T-03-09

Silicon Epitaxial Planar Type

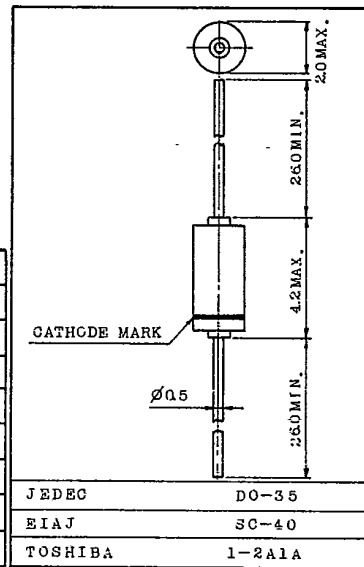
Diode

1N4606

TENTATIVE

COMMUNICATION AND INDUSTRIAL APPLICATIONS.
HIGH VOLTAGE, ULTRA HIGH SPEED SWITCHING APPLICATIONS.

Unit in mm



Weight : 0.14g

MAXIMUM RATINGS (Ta=25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Maximum (Peak) Reverse Voltage	V _{RM}	85	V
Reverse Voltage	V _R	70	V
Maximum (Peak) Forward Current	I _{FM}	600	mA
Average Forward Current	I _O	200	mA
Surge Current (1 μs)	I _{FSM}	4	A
Power Dissipation	P	500	mW
Junction Temperature	T _j	200	°C
Storage Temperature Range	T _{stg}	-65 ~ 200	°C

ELECTRICAL CHARACTERISTICS (Ta=25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Breakdown Voltage	V _{BR}	I _R =100μA	85	-	-	V
Forward Voltage	V _F (1)	I _F =100μA	0.54	0.60	0.66	V
	V _F (2)	I _F =1mA	0.65	0.71	0.77	V
	V _F (3)	I _F =10mA	0.74	0.80	0.86	V
	V _F (4)	I _F =100mA	0.79	0.86	0.92	V
	V _F (5)	I _F =200mA	0.86	0.93	1.00	V
	V _F (6)	I _F =250mA	-	-	1.10	V
Reverse Current	I _R (1)	V _R =50V	-	-	100	nA
	I _R (2)	V _R =50V, Ta=100°C	-	-	25	μA
	I _R (3)	V _R =70V	-	-	250	nA
Total Capacitance	C _T	V _R =0, f=1MHz	-	-	2.5	pF
Reverse Recovery Time	t _{rr} (1)	I _F =I _R =10mA, I _{rr} =1mA	-	-	6	ns
	t _{rr} (2)	I _F =I _R =10 ~ 200mA I _{rr} =0.1 I _F	-	-	4	ns
	t _{rr} (3)	I _F =I _R =200 ~ 400mA I _{rr} =0.1 I _F	-	-	6	ns

TOSHIBA CORPORATION

This datasheet has been downloaded from:

www.DatasheetCatalog.com

Datasheets for electronic components.



LittleDiode supplies new, hard to find or obsolete electronic components and semiconductors all over the world.

With over two million different components listed you are sure to find the part you need.

Feel free to visit us today at our online store:

LittleDiode.com

Looking forward to providing you with the best possible service.